Abstracts

A 26.5-40.0 GHz GaAs FET Amplifier

J. Rosenberg, P. Chye, C. Haung and G. Policky. "A 26.5-40.0 GHz GaAs FET Amplifier." 1982 MTT-S International Microwave Symposium Digest 82.1 (1982 [MWSYM]): 166-168.

Sub-half-micron gate GaAs FET's have been used to fabricate a MIC balanced amplifier module with 4.2 dB of minimum gain over 26.5-40.0 GHz. The module and devices are described and data is presented for gain, VSWR, noise figure, and power on the module.

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